MA4X193

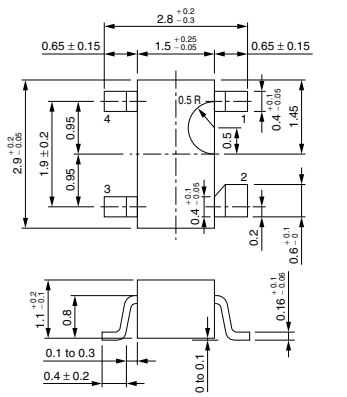
Silicon epitaxial planar type

Silicon epitaxial planar type

■ Features

- Mini type 4-pin package, contained four elements
- Short reverse recovery time t_{rr}
- Bridge diodes for surface mounting
- Anode common + cathode common composite product

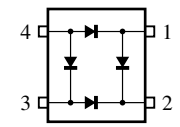
Unit : mm



1: Cathode 1 Anode 2
2: Cathode 2, 3
3: Anode 3 Cathode 4
4: Anode 1, 4
Mini Type Package (4-pin)

Marking Symbol: M2Z

Internal Connection



■ Absolute Maximum Ratings $T_a = 25°C$

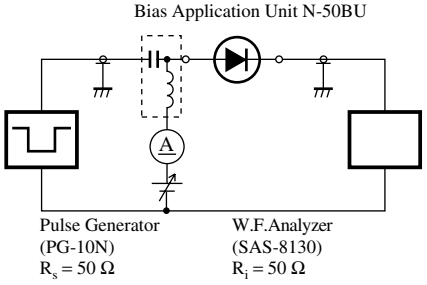
Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	80	V
Repetitive peak reverse voltage	V_{RRM}	80	V
Average forward current	$I_{F(AV)}$	70	mA
Repetitive peak forward current	I_{FRM}	150	mA
Non-repetitive peak forward surge current*	I_{FSM}	250	mA
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	−55 to +150	°C

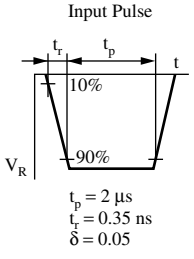
Note) * : t = 1 s

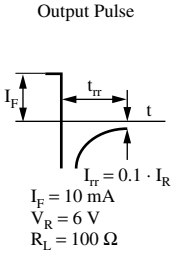
■ Electrical Characteristics $T_a = 25°C$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	V_R = 75 V			100	nA
Forward voltage (DC)	V_F	I_F = 70 mA			1.2	V
Reverse voltage (DC)	V_R	I_R = 100 µA	80			V
Terminal capacitance	C_t	V_R = 0 V, f = 1 MHz			15	pF
Reverse recovery time*	t_{rr}	I_F = 10 mA, V_R = 6 V I_{rr} = 0.1 · I_R, R_L = 100 Ω			10	ns

Note) 1. Rated input/output frequency: 100 MHz
2. * : t_{rr} measuring circuit

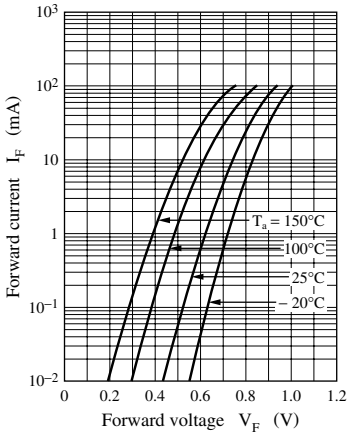




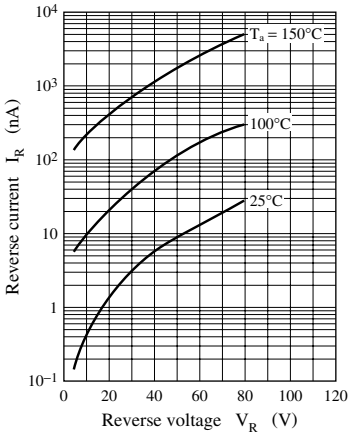


4-1 and 4-3 pins (anode common) characteristics charts

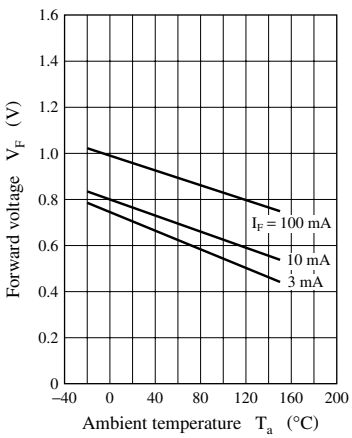
I_F — V_F



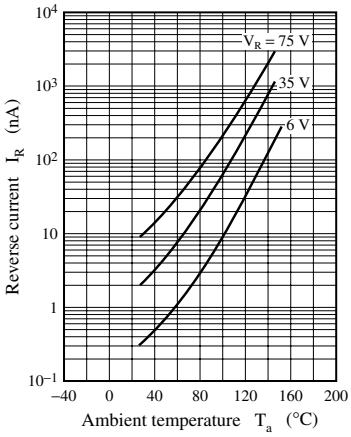
I_R — V_R



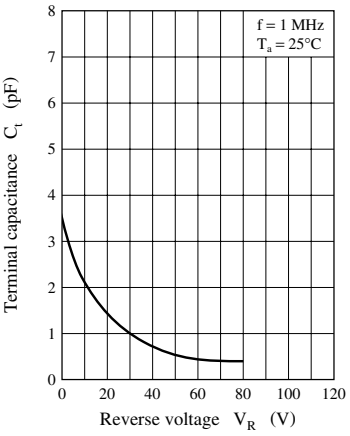
V_F — T_a



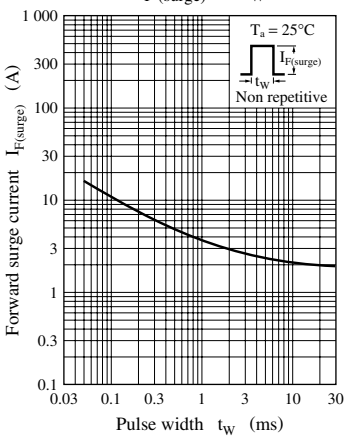
I_R — T_a



C_t — V_R

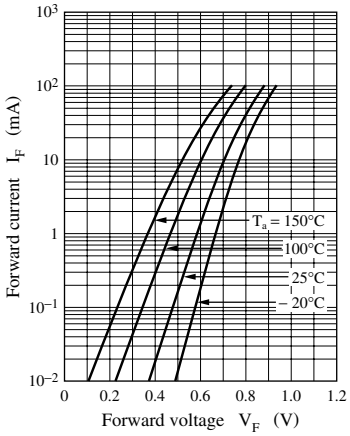


$I_{F\,(surge)}$ — t_W

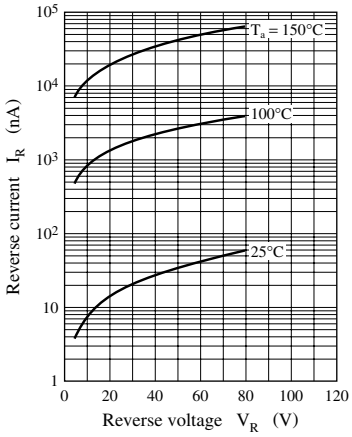


1-2 and 3-2 pins (cathode common) characteristics charts

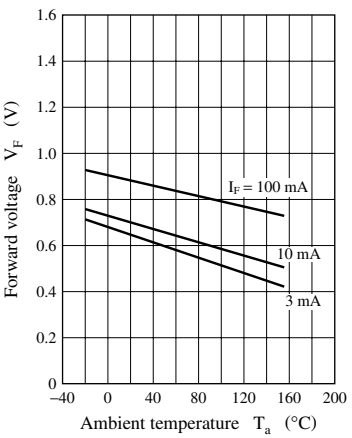
I_F — V_F



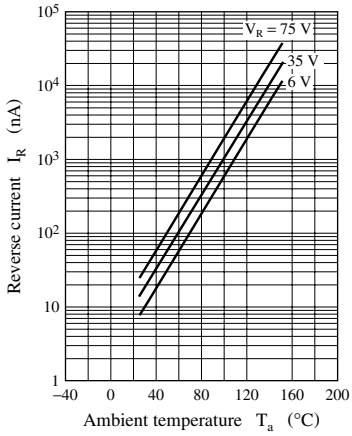
I_R — V_R



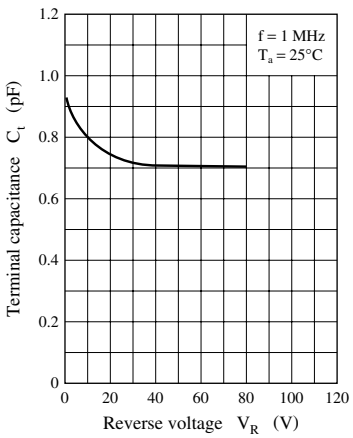
V_F — T_a



I_R — T_a



C_t — V_R



$I_{F\,(surge)}$ — t_W

